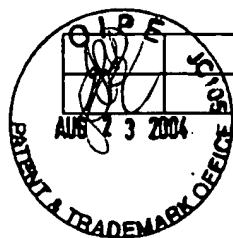


## Section 2. Form PTO - 1449 (Modified) (ATTACHMENT)

FORM PTO-1449 U.S. DEPT. OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. QIL-1CDV	SERIAL NO. 10/763,461
	APPLICANT Shchukin et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	FILING DATE 1/23/04	GROUP 2811

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### FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

Exam Initial	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB	TRANSLATION YES   NO

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## Section 2. Form PTO - 1449 (Modified) (ATTACHMENT)

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	APPLICANT Shchukin et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	FILING DATE January 23, 2004	GROUP 2815

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## FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

Exam Initial	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB	TRANSLATION YES   NO
<i>[Signature]</i>	WO02/13273	02/14/02	WIPO	H01L	29/06	X

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Greg. Maldonado	12/07/2005